

SRAM Cell and Methods of Fabrication

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprises a substrate. In addition, the semiconductor device comprises an active region and an isolation region. The active region is in the substrate and comprises a semiconductor material. The isolation region is also in the substrate, adjacent the active region and comprises an insulating material. The active region and isolation region form a surface having a step therein. The semiconductor further comprises a dielectric material formed over the step. The dielectric material has a dielectric constant greater than about 8.
(FIG. 2a)